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Document Number: K12P48M50SF4
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K12P48M50SF4

K12 Sub-Family

Supports the following:
MK12DX128VLF5, MK12DX256VLF5

Features

- Operating Characteristics
  - Voltage range: 1.71 to 3.6 V
  - Flash write voltage range: 1.71 to 3.6 V
  - Temperature range (ambient): -40 to 105°C
- Performance
  - Up to 50 MHz ARM Cortex-M4 core with DSP instructions delivering 1.25 Dhrystone MIPS per MHz
- Memories and memory interfaces
  - Up to 256 KB program flash for devices with FlexNVM.
  - 64 KB FlexNVM on FlexMemory devices
  - 4 KB FlexRAM on FlexMemory devices
  - Up to 64 KB RAM
  - Serial programming interface (EzPort)
- Clocks
  - 3 to 32 MHz crystal oscillator
  - 32 kHz crystal oscillator
  - Multi-purpose clock generator
- System peripherals
  - Multiple low-power modes to provide power optimization based on application requirements
  - 16-channel DMA controller, supporting up to 63 request sources
  - External watchdog monitor
  - Software watchdog
  - Low-leakage wakeup unit

- Security and integrity modules
  - Hardware CRC module to support fast cyclic redundancy checks
  - 128-bit unique identification (ID) number per chip
- Human-machine interface
  - General-purpose input/output
- Analog modules
  - 16-bit SAR ADC
  - Two analog comparators (CMP) containing a 6-bit DAC and programmable reference input
  - Voltage reference
- Timers
  - Programmable delay block
  - Eight-channel motor control/general purpose/PWM timer
  - Two 2-channel general purpose timers, one with quadrature decoder functionality
  - Periodic interrupt timers
  - 16-bit low-power timer
  - Carrier modulator transmitter
  - Real-time clock
- Communication interfaces
  - USB Device Charger detect
  - SPI module
  - I2C module
  - Four UART modules
  - I2S module

Table of Contents

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to freescale.com and perform a part number search for the following device numbers: PK12 and MK12 .

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q K## A M FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
K##	Kinetis family	• K12
A	Key attribute	• D = Cortex-M4 w/ DSP • F = Cortex-M4 w/ DSP and FPU
M	Flash memory type	• N = Program flash only • X = Program flash and FlexMemory

Table continues on the next page...

Field	Description	Values
FFF	Program flash memory size	• 32 = 32 KB • 64 = 64 KB • 128 = 128 KB • 256 = 256 KB • 512 = 512 KB • 1M0 = 1 MB • 2M0 = 2 MB
R	Silicon revision	• Z = Initial • (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = –40 to 105 • C = –40 to 85
PP	Package identifier	• FM = 32 QFN (5 mm x 5 mm) • FT = 48 QFN (7 mm x 7 mm) • LF = 48 LQFP (7 mm x 7 mm) • LH = 64 LQFP (10 mm x 10 mm) • MP = 64 MAPBGA (5 mm x 5 mm) • LK = 80 LQFP (12 mm x 12 mm) • LL = 100 LQFP (14 mm x 14 mm) • MC = 121 MAPBGA (8 mm x 8 mm) • LQ = 144 LQFP (20 mm x 20 mm) • MD = 144 MAPBGA (13 mm x 13 mm)
CC	Maximum CPU frequency (MHz)	• 5 = 50 MHz • 7 = 72 MHz • 10 = 100 MHz • 12 = 120 MHz • 15 = 150 MHz • 18 = 180 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

MK12DX256VLF5

2.5 Small package marking

In an effort to save space, small package devices use special marking on the chip. These markings have the following format:

Q ## C F T PP

This table lists the possible values for each field in the part number for small packages (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
C	Speed	• G = 50 MHz
F	Flash memory configuration	• G = 128 KB + Flex • H = 256 KB + Flex • 9 = 512 KB
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• MC = 121 MAPBGA

This tables lists some examples of small package marking along with the original part numbers:

Original part number	Alternate part number
MK12DX256VLF5	M12GHVLF
MK12DN512VLH5	M12G9VLH

3 Terminology and guidelines

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior:

Symbol	Description	Min.	Max.	Unit
I_{WP}	Digital I/O weak pullup/ pulldown current	10	130	µA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

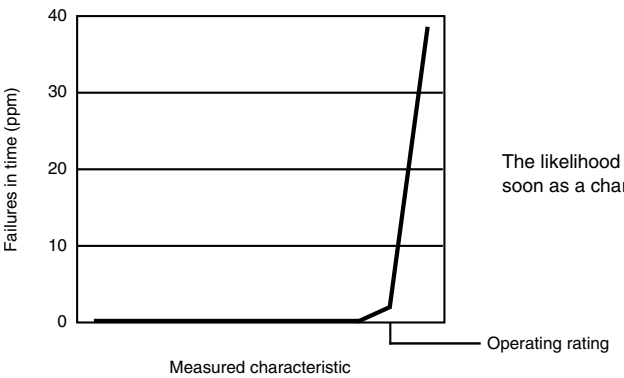
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

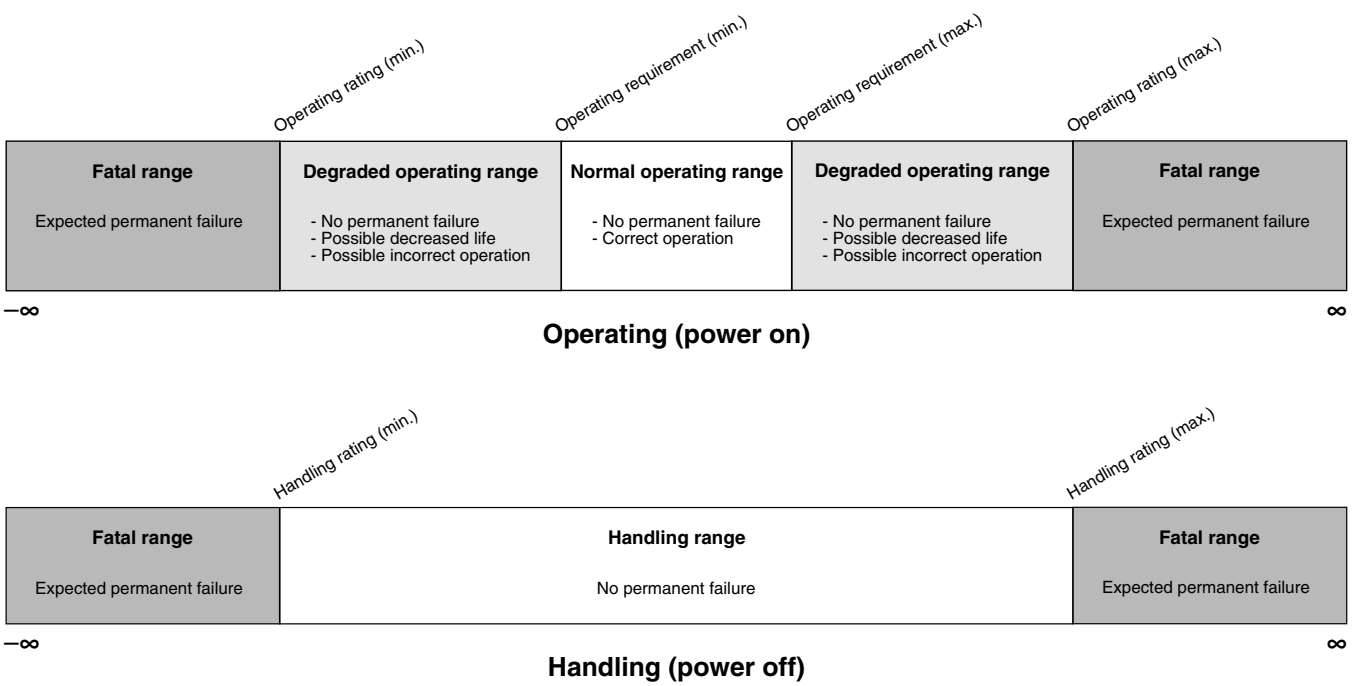
Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

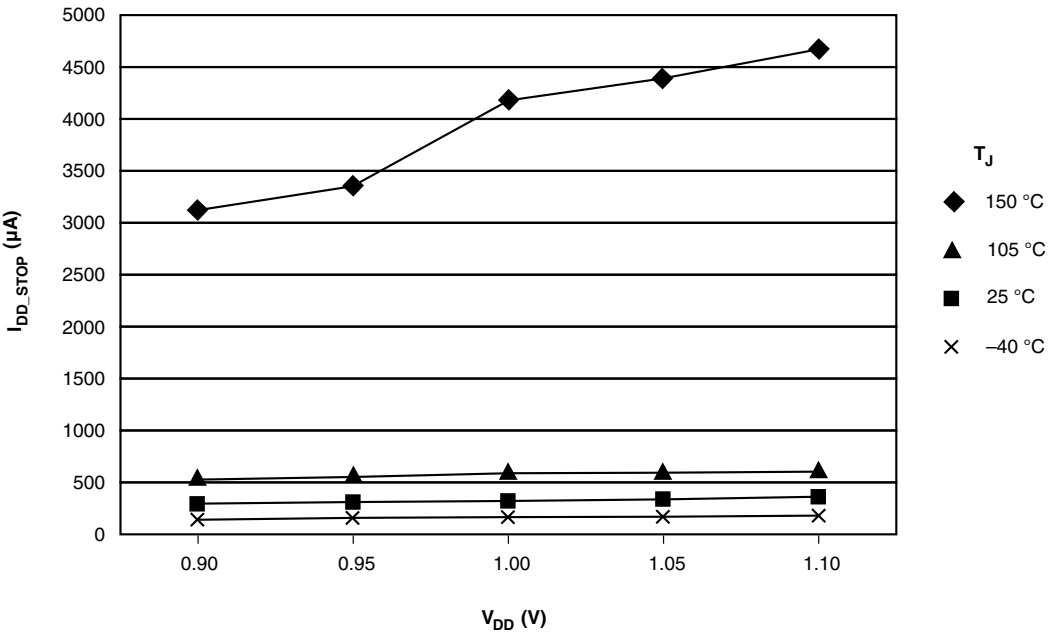
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	155	mA
V_{DIO}	Digital input voltage (except $\overline{\text{RESET}}$, EXTAL, and XTAL)	–0.3		V
V_{AIO}	Analog[1], $\overline{\text{RESET}}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Maximum current single pin limit (applies to all digital pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
VREGIN	USB regulator input	–0.3	6.0	V
V_{BAT}	RTC battery supply voltage	–0.3	3.8	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

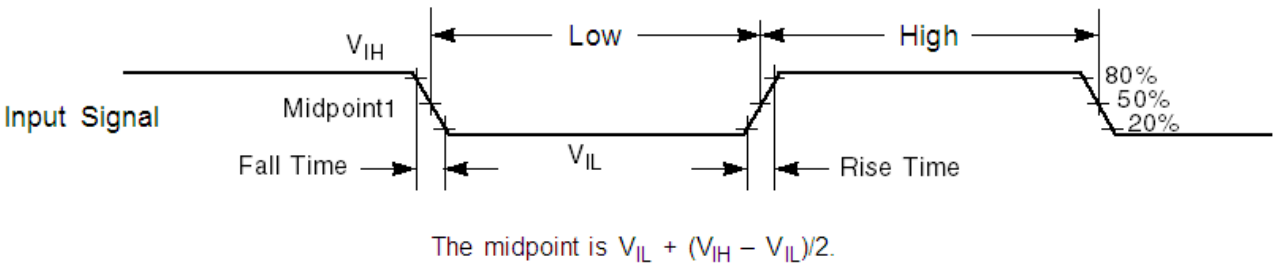


Figure 1. Input signal measurement reference

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 0.7 × V_{DD} 0.75 × V_{DD}	 — —	 V V	
V_{IL}	Input low voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 — —	 0.35 × V_{DD} 0.3 × V_{DD}	 V V	
V_{HYS}	Input hysteresis	0.06 × V_{DD}	—	V	
I_{ICIO}	I/O pin DC injection current — single pin • V_{IN} < V_{SS}-0.3V (Negative current injection) • V_{IN} > V_{DD}+0.3V (Positive current injection)	 -3 —	 — +3	 mA	1

Table continues on the next page...

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	 -25 —	 — +25	 mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is less than V_{AIO_MIN} or greater than V_{AIO_MAX}, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO\_MIN}-V_{IN})/|I_{ICAIO}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO\_MAX})/|I_{ICAIO}|$. Select the larger of these two calculated resistances if the pin is exposed to positive and negative injection currents.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V_{LVW1H}	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	80	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	µs	

1. Rising threshold is the sum of falling threshold and hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

5.2.3 Voltage and current operating behaviors

Table 4. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = - 9 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -3 mA	V_{DD} – 0.5	—	V	
	Output high voltage — low drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -2 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -0.6 mA	V_{DD} – 0.5	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — high drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 9 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 3 mA	—	0.5	V	
	Output low voltage — low drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 2 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 0.6 mA	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin)				
	• @ full temperature range	—	1.0	µA	1
	• @ 25 °C	—	0.1	µA	
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	µA	
I_{OZ}	Total Hi-Z (off-state) leakage current (all input pins)	—	4	µA	
R_{PU}	Internal pullup resistors	22	50	kΩ	2
R_{PD}	Internal pulldown resistors	22	50	kΩ	3

1. Tested by ganged leakage method
2. Measured at Vinput = V_{SS}
3. Measured at Vinput = V_{DD}

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR}, and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 50 MHz
- Bus clock = 50 MHz
- Flash clock = 25 MHz
- MCG mode: FEI

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip. • 1.71 V/(V_{DD} slew rate) ≤ 300 µs • 1.71 V/(V_{DD} slew rate) > 300 µs	 — —	 300 1.7 V / (V_{DD} slew rate)	µs	1
	• VLLS0 → RUN	—	135	µs	
	• VLLS1 → RUN	—	135	µs	
	• VLLS2 → RUN	—	85	µs	
	• VLLS3 → RUN	—	85	µs	
	• LLS → RUN	—	6	µs	
	• VLPS → RUN	—	5.2	µs	
	• STOP → RUN	—	5.2	µs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash • @ 1.8 V • @ 3.0 V	 — —	 12.98 12.93	 14 13.8	 mA mA	2

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					3, 4
	• @ 1.8 V	—	17.04	19.3	mA	
	• @ 3.0 V					
	• @ 25°C	—	17.01	18.9	mA	
	• @ 125°C	—	19.8	21.3	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	7.95	9.5	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	5.88	7.4	mA	5
I_{DD_STOP}	Stop mode current at 3.0 V	—			μA	
	• @ –40 to 25°C		320	436		
	• @ 50°C		360	489		
	• @ 70°C		410	620		
	• @ 105°C		610	1100		
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	754	—	μA	6
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	1.1	—	mA	7
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V	—	437	—	μA	8
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V	—			μA	
	• @ –40 to 25°C		7.33	24.2		
	• @ 50°C		14	32		
	• @ 70°C		28	48		
	• @ 105°C		110	280		
I_{DD_LLS}	Low leakage stop mode current at 3.0 V	—			μA	
	• @ –40 to 25°C		3.14	4.8		
	• @ 50°C		6.48	28.3		
	• @ 70°C		13.85	44.6		
	• @ 105°C		55.53	71.3		
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V	—			μA	
	• @ –40 to 25°C		2.19	3.4		
	• @ 50°C		4.35	4.35		
	• @ 70°C		8.92	24.6		
	• @ 105°C		35.33	45.3		
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V	—			μA	
	• @ –40 to 25°C		1.77	3.1		
	• @ 50°C		2.81	13.8		
	• @ 70°C		5.20	22.3		
	• @ 105°C		19.88	34.2		

Table continues on the next page...

Table 6. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	1.03 1.92 4.03 17.43	1.8 7.5 15.9 28.7	µA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.543 1.36 3.39 16.52	1.1 7.58 14.3 24.1	µA	
I_{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.359 1.03 2.87 15.20	0.95 6.8 15.4 25.3	µA	
I_{DD_VBAT}	Average current when CPU is not accessing RTC registers at 3.0 V • @ –40 to 25°C • @ 50°C • @ 70°C • @ 105°C	—	0.91 1.1 1.5 4.3	1.1 1.35 1.85 5.7	µA	9

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks disabled.
3. 50 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled, and peripherals are in active operation.
4. Max values are measured with CPU executing DSP instructions
5. 25 MHz core and system clock, 25 MHz bus clock, and 12.5 MHz flash clock. MCG configured for FEI mode.
6. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
7. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled but peripherals are not in active operation. Code executing from flash.
8. 4 MHz core, system, and bus clock and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.
9. Includes 32 kHz oscillator current and RTC operation.

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode
- USB regulator disabled
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL

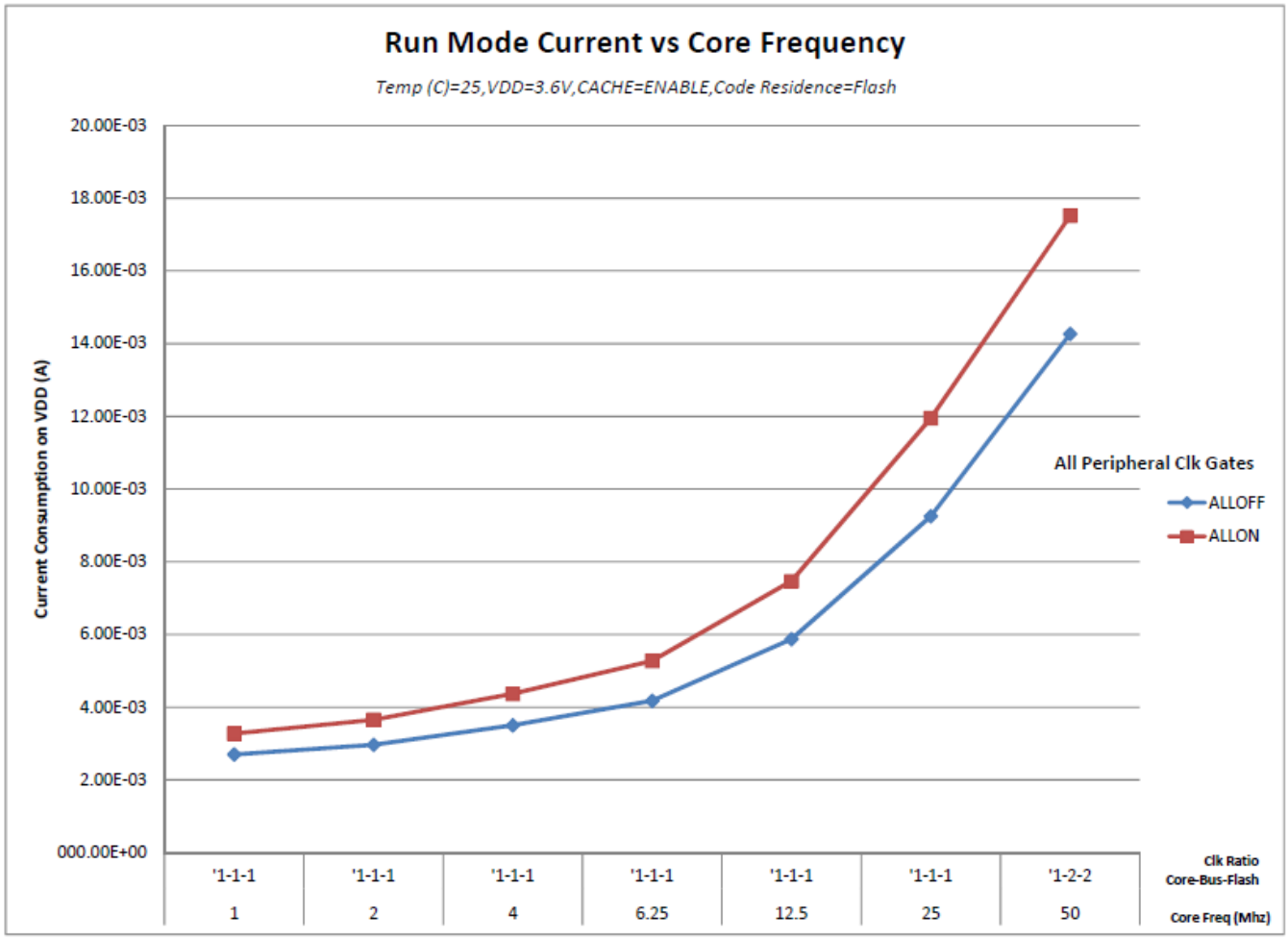


Figure 2. Run mode supply current vs. core frequency

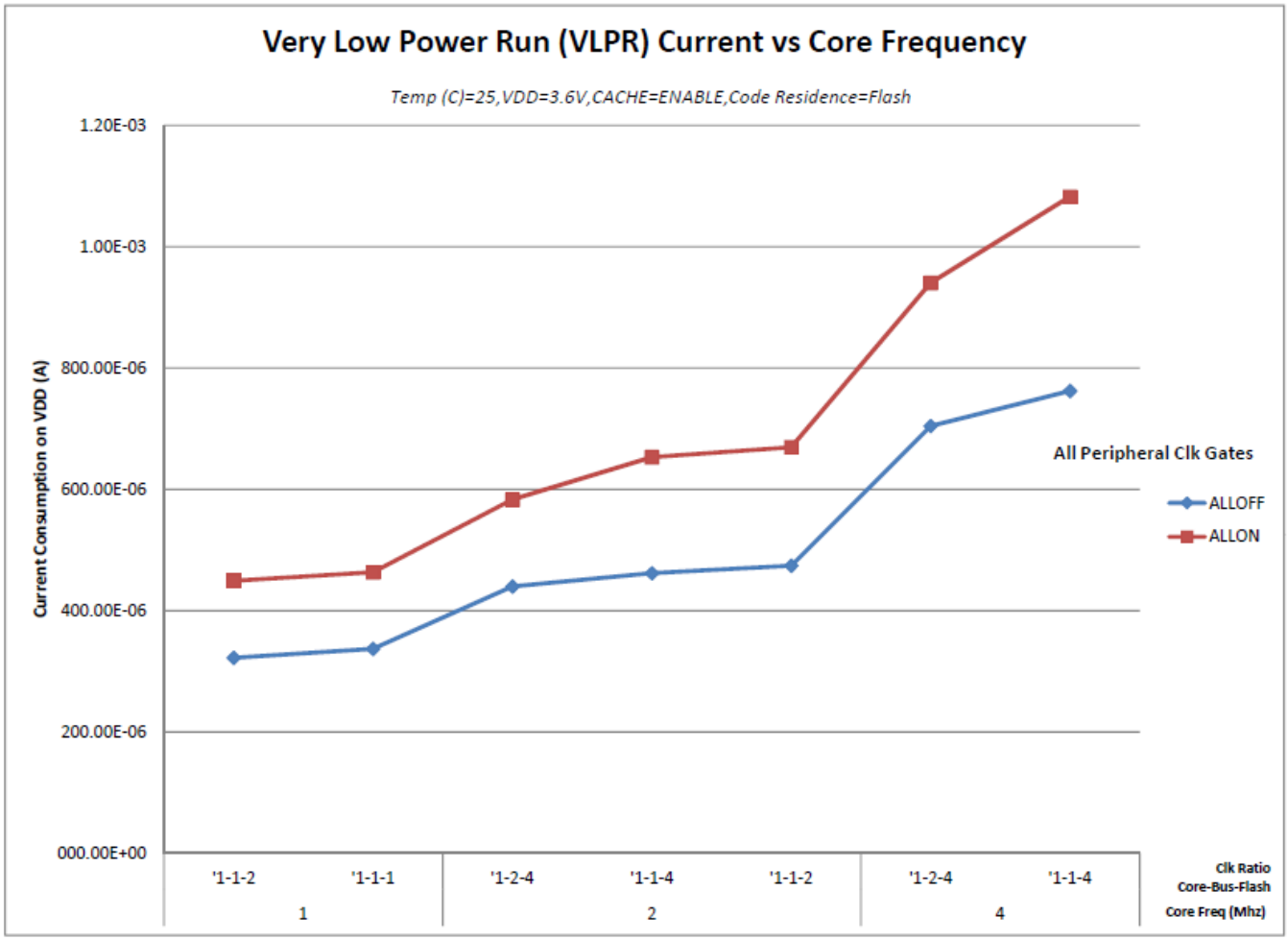


Figure 3. VLPR mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors [1]

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	19	dBµV	2, 3
V_{RE2}	Radiated emissions voltage, band 2	50–150	21	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	19	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	11	dBµV	
V_{RE_IEC}	IEC level	0.15–1000	L	—	3, 4

1. This data was collected on a MK20DN128VLH5 64pin LQFP device.
2. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

3. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 12 MHz (crystal), f_{SYS} = 48 MHz, f_{BUS} = 48MHz
4. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for "EMC design."

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	50	MHz	
f_{BUS}	Bus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode[1]					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	
f_{FLASH}	Flash clock	—	1	MHz	
f_{ERCLK}	External reference clock	—	16	MHz	
f_{LPTMR_pin}	LPTMR clock	—	25	MHz	
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
f_{I2S_MCLK}	I2S master clock	—	12.5	MHz	
f_{I2S_BCLK}	I2S bit clock	—	4	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

5.3.2 General switching specifications

These general purpose specifications apply to all pins configured for:

- GPIO signaling
- Other peripheral module signaling not explicitly stated elsewhere

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1, 2
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) — Asynchronous path	100	—	ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	50	—	ns	3
	External reset pulse width (digital glitch filter disabled)	100	—	ns	3
	Port rise and fall time (high drive strength) • Slew disabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$ • Slew enabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$	 — — — —	 13 7 36 24	 ns ns ns ns	4
	Port rise and fall time (low drive strength) • Slew disabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$ • Slew enabled • $1.71 \le V_{DD} \le 2.7V$ • $2.7 \le V_{DD} \le 3.6V$	 — — — —	 12 6 36 24	 ns ns ns ns	5

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater synchronous and asynchronous timing must be met.
3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
4. 75 pF load
5. 15 pF load

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	125	°C
T_A	Ambient temperature	–40	105	°C

5.4.2 Thermal attributes

Board type	Symbol	Description	48 LQFP	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	70	°C/W	1, 2
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	47	°C/W	1, 3
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	58	°C/W	1,3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	40	°C/W	1,3
—	$R_{\theta JB}$	Thermal resistance, junction to board	24	°C/W	4
—	$R_{\theta JC}$	Thermal resistance, junction to case	18	°C/W	5
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	3	°C/W	6

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)* with the single layer board horizontal. For the LQFP, the board meets the JESD51-3 specification. For the MAPBGA, the board meets the JESD51-9 specification.

3. Determined according to JEDEC Standard JESD51-6, *Integrated Circuits Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)* with the board horizontal.
4. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*. Board temperature is measured on the top surface of the board near the package.
5. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
6. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 JTAG electricals

Table 12. JTAG limited voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
J1	TCLK frequency of operation			MHz
	• Boundary Scan	0	10	
	• JTAG and CJTAG	0	25	
	• Serial Wire Debug	0	50	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	20	—	ns
	• Serial Wire Debug	10	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	17	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

Table 13. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	• Boundary Scan	0	10	
	• JTAG and CJTAG	0	20	
	• Serial Wire Debug	0	40	
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width			
	• Boundary Scan	50	—	ns
	• JTAG and CJTAG	25	—	ns
	• Serial Wire Debug	12.5	—	ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1.4	—	ns
J11	TCLK low to TDO data valid	—	22.1	ns
J12	TCLK low to TDO high-Z	—	22.1	ns
J13	$\overline{\text{TRST}}$ assert time	100	—	ns
J14	$\overline{\text{TRST}}$ setup time (negation) to TCLK high	8	—	ns

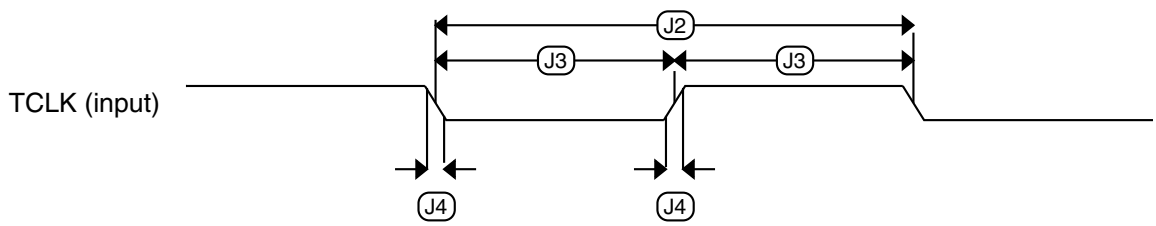


Figure 4. Test clock input timing

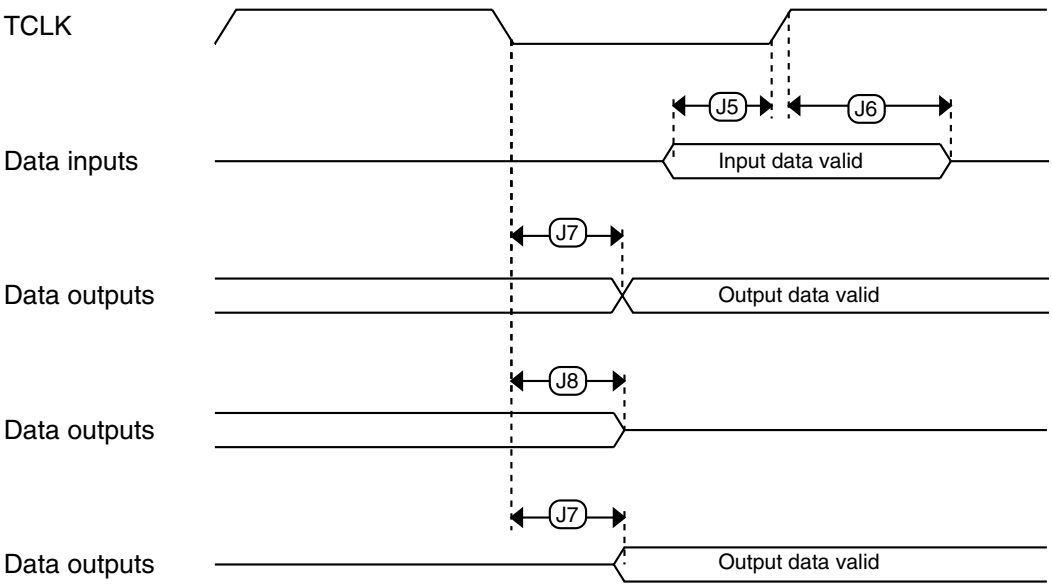


Figure 5. Boundary scan (JTAG) timing

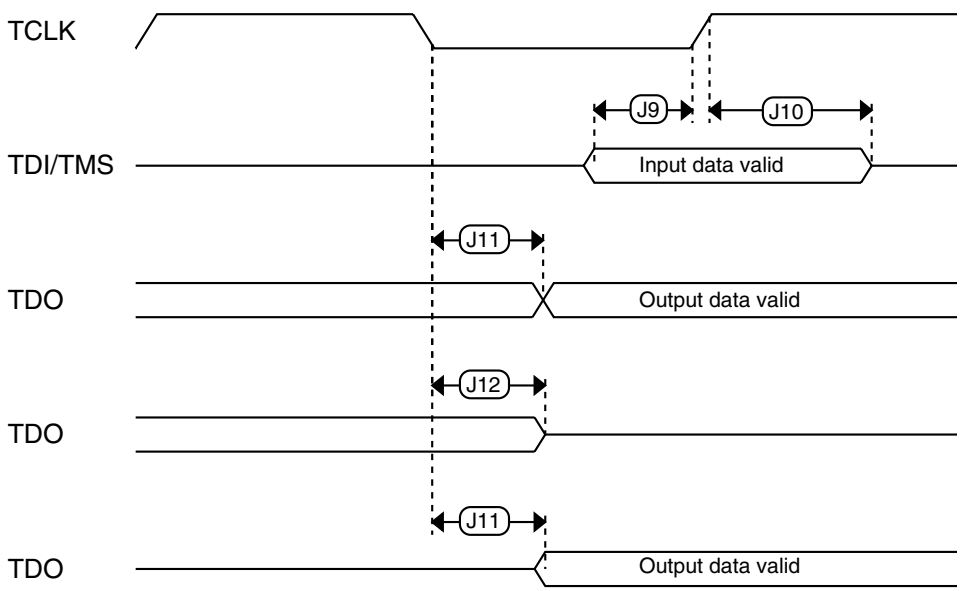


Figure 6. Test Access Port timing

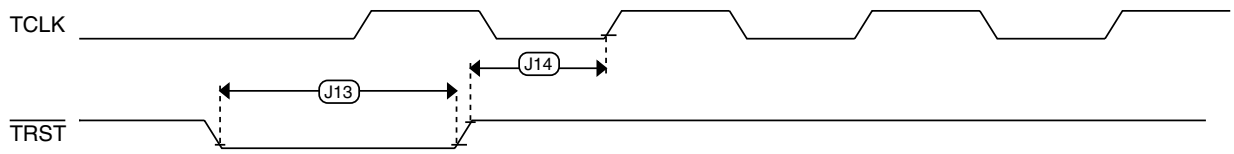


Figure 7. TRST timing

6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

6.3.1 MCG specifications

Table 14. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C	—	32.768	—	kHz	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	—	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	—	± 0.3	± 0.6	$\%f_{dco}$	1
$\Delta f_{dco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM only	—	± 0.2	± 0.5	$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature	—	+0.5/-0.7	± 2	$\%f_{dco}$	1, 2
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C	—	± 0.3	±1	$\%f_{dco}$	1, 2
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C	—	4	—	MHz	
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C	3	—	5	MHz	
f_{loc_low}	Loss of external clock minimum frequency — RANGE = 00	(3/5) x f_{ints_t}	—	—	kHz	
f_{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11	(16/5) x f_{ints_t}	—	—	kHz	

Table continues on the next page...